

N-Channel Enhancement Mode Power MOSFET

**Description**

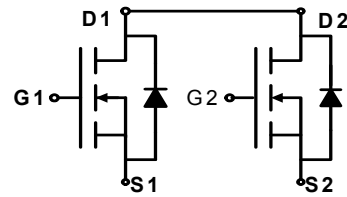
The PE8205 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

**General Features**

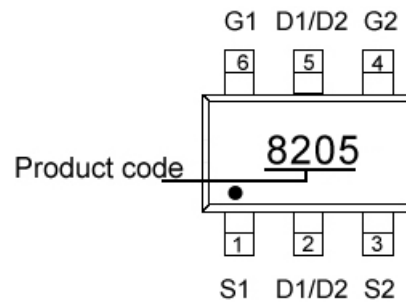
- $V_{DS} = 20V, I_D = 6A$   
 $R_{DS(ON)} < 34m\Omega @ V_{GS}=2.5V$   
 $R_{DS(ON)} < 24m\Omega @ V_{GS}=4.5V$
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

**Application**

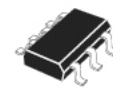
- Battery protection
- Load switch
- Power management



Schematic diagram



Marking and pin Assignment



SOT23-6 top view

**Absolute Maximum Ratings (TA=25°C unless otherwise noted)**

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 10$	V
Drain Current-Continuous	$I_D$	6	A
Drain Current-Pulsed (Note 1)	$I_{DM}$	25	A
Maximum Power Dissipation	$P_D$	1.5	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

**Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	83	°C/W
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**Electrical Characteristics (TA=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	20	21	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=19.5V, V_{GS}=0V$	-	-	1	$\mu A$

Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 10V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	0.7	1.2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=4.5V, I_D=4.5A$	18	20	24	m $\Omega$
		$V_{GS}=2.5V, I_D=3.5A$	23	26	34	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=4.5A$	-	10	-	S
<b>Dynamic Characteristics (Note4)</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=8V, V_{GS}=0V,$ $F=1.0MHz$	-	600	-	PF
Output Capacitance	$C_{oss}$		-	330	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	140	-	PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, I_D=1A$ $V_{GS}=4.5V, R_{GEN}=6\Omega$	-	10	20	nS
Turn-on Rise Time	$t_r$		-	11	25	nS
Turn-Off Delay Time	$t_{d(off)}$		-	35	70	nS
Turn-Off Fall Time	$t_f$		-	30	60	nS
Total Gate Charge	$Q_g$	$V_{DS}=10V, I_D=6A,$ $V_{GS}=4.5V$	-	10	15	nC
Gate-Source Charge	$Q_{gs}$		-	2.3	-	nC
Gate-Drain Charge	$Q_{gd}$		-	1.5	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=1.7A$	-	0.75	1.2	V
Diode Forward Current (Note 2)	$I_S$		-	-	1.7	A

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

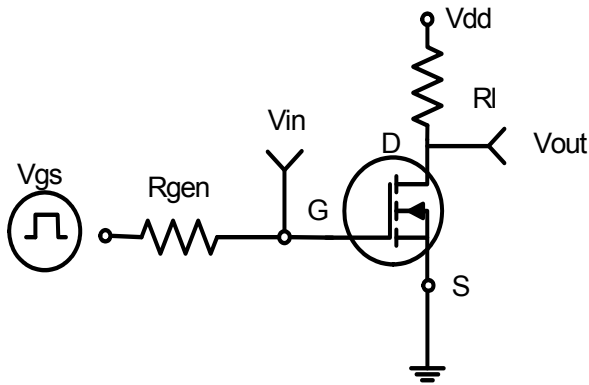


Figure 1: Switching Test Circuit

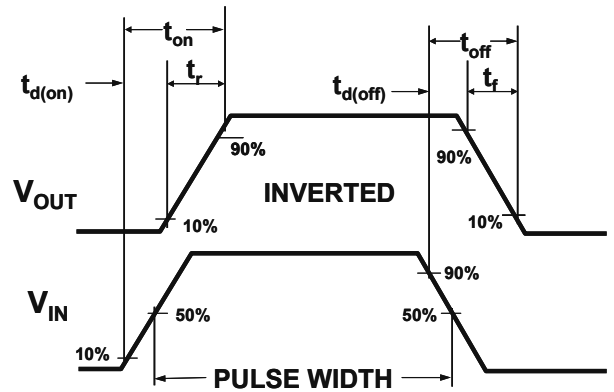


Figure 2: Switching Waveforms

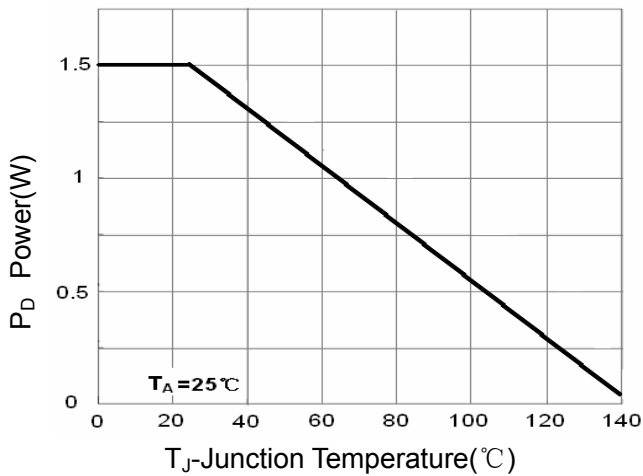


Figure 3 Power Dissipation

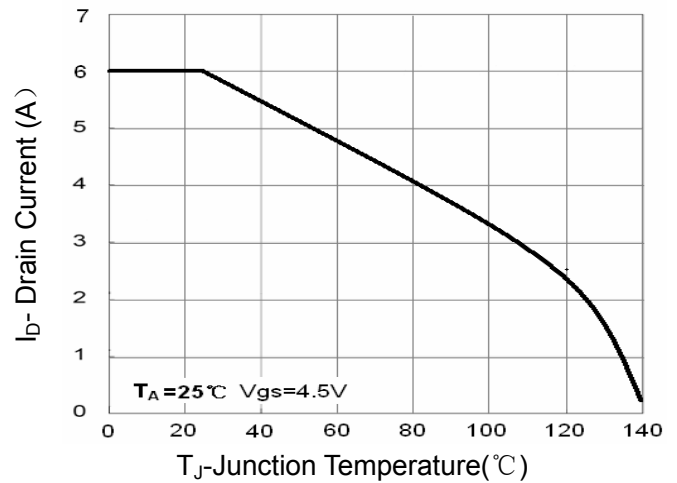


Figure 4 Drain Current

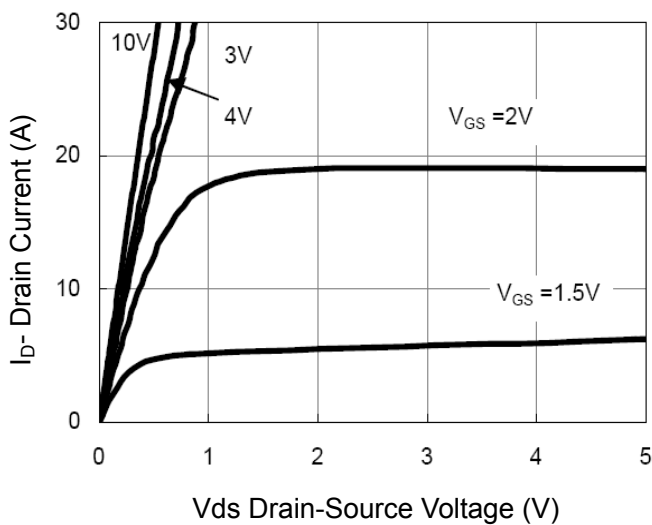


Figure 5 Output CHARACTERISTICS

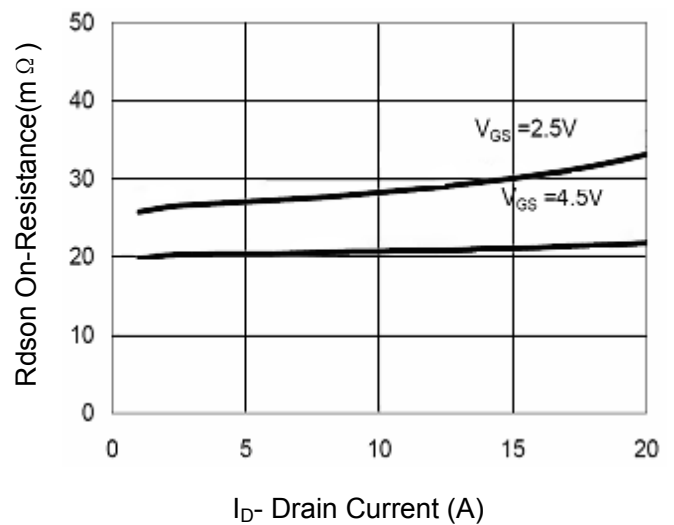


Figure 6 Drain-Source On-Resistance

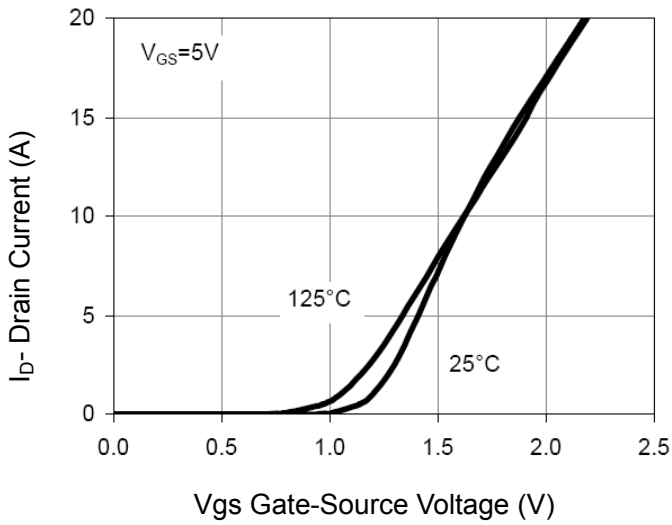


Figure 7 Transfer Characteristics

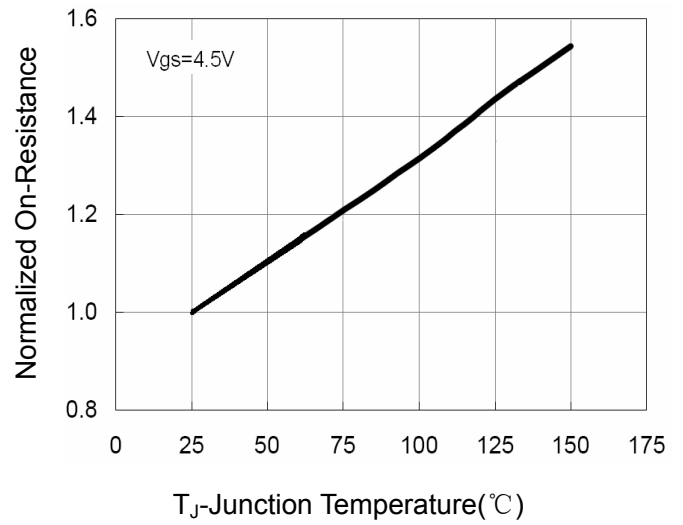


Figure 8 Drain-Source On-Resistance

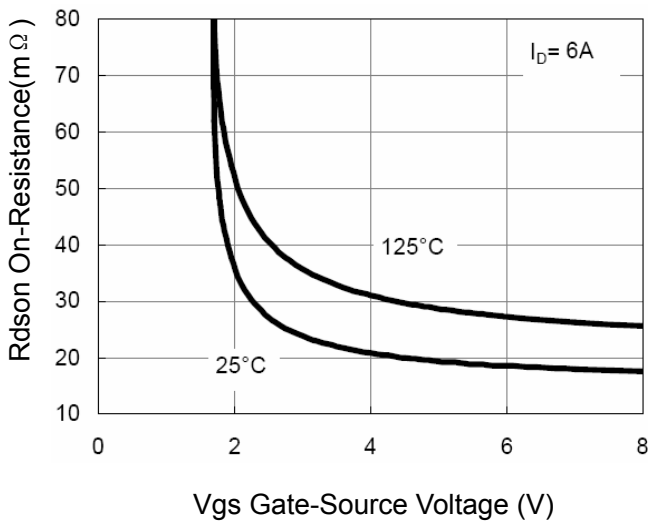


Figure 9  $R_{DS(on)}$  vs  $V_{GS}$

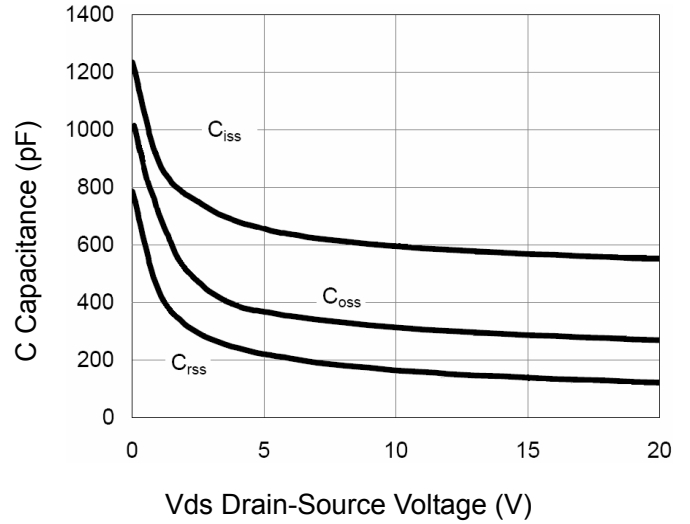


Figure 10 Capacitance vs  $V_{DS}$

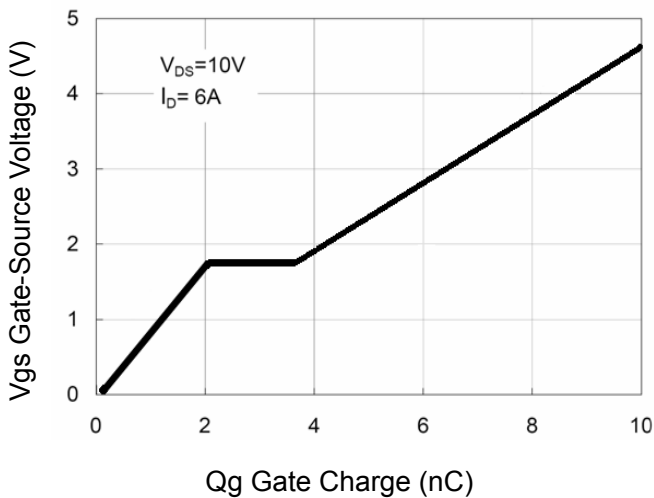


Figure 11 Gate Charge

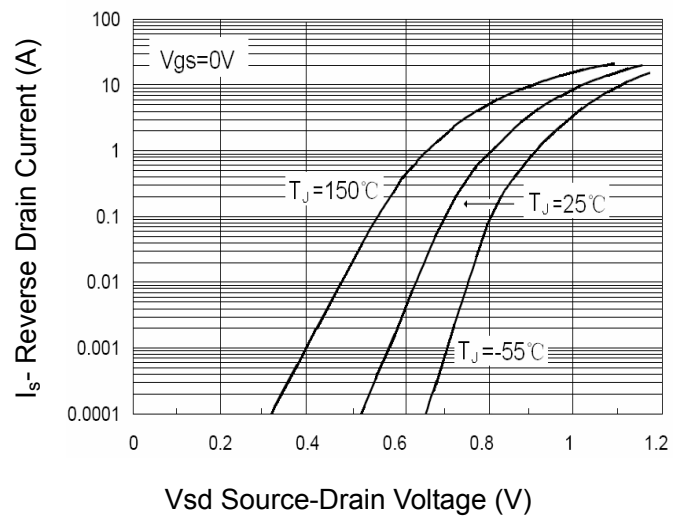


Figure 12 Source- Drain Diode Forward

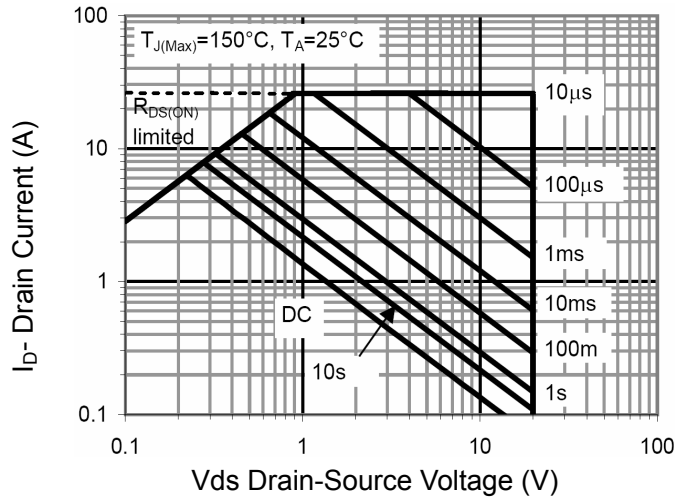


Figure 13 Safe Operation Area

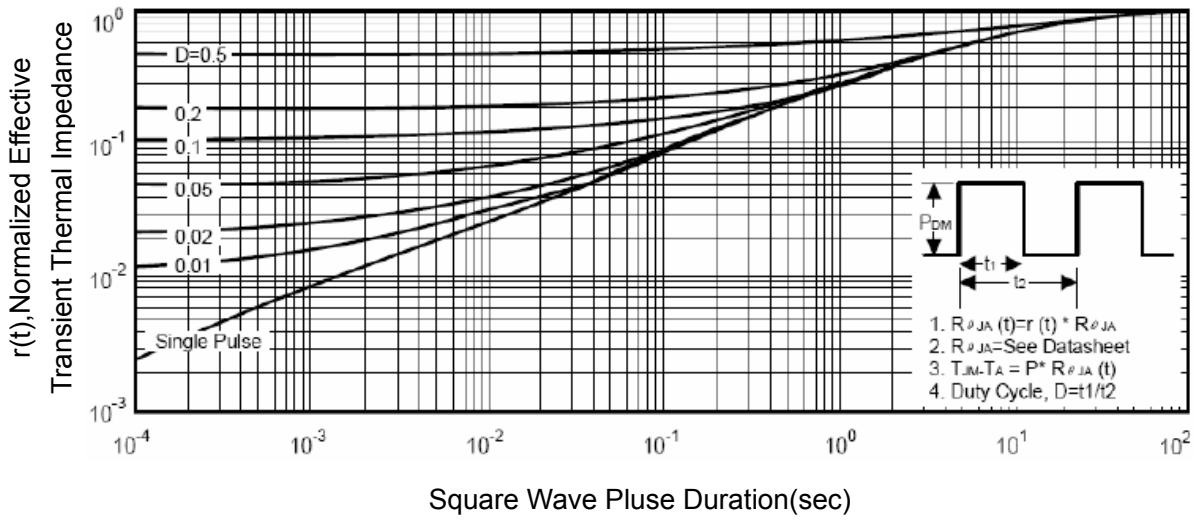


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT23-6 PACKAGE INFORMATION

